

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **TPV595A** is Designed for Class AB Push Pull, Common Emitter from 470 to 860 MHz Applications.

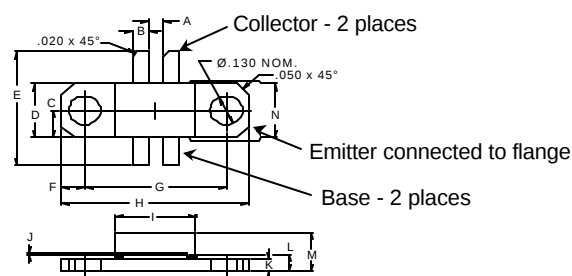
FEATURES:

- Gold Metalization
- Emitter Ballast Resistors
- Internal Input Matching

MAXIMUM RATINGS

I_C	2 x 2.6 A
V_{CB}	45 V
P_{DISS}	65 W @ T _C = 25 °C
T_J	-50 °C to +200 °C
T_{STG}	-50 °C to +200 °C
α_{JC}	2.5 °C/W

PACKAGE STYLE .250 BAL FLG



DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.060 / 1.52	
B	.055 / 1.40	.065 / 1.65
C	.125 / 3.18	
D	.243 / 6.17	.255 / 6.48
E	.630 / 16.00	.670 / 17.01
F	.092 / 2.34	
G	.555 / 14.10	.565 / 14.35
H	.739 / 18.77	.750 / 19.05
I	.315 / 8.00	.327 / 8.31
J	.002 / 0.05	.006 / 0.15
K	.055 / 1.40	.065 / 1.65
L	.075 / 1.91	.095 / 2.41
M		.190 / 4.83
N	.245 / 6.22	.257 / 6.53

Order Code: **ASI10835**

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 40 mA	25	28		V
BV_{CER}	I _C = 20 mA R _{BE} = 51 Ω	40			V
BV_{CBO}	I _C = 20 mA	45			V
I_{CBO}	V _{CB} = 20 V			5.0	mA
BV_{EBO}	I _E = 5 mA	3.0			V
h_{FE}	V _{CE} = 20 V I _C = 500 mA	10			--
C_{OB}	V _{CB} = 25 V			20	pF
P_G	V _{CE} = 25 V I _C = 2 x 900 mA P _{REF} = 14 W	8.5	9.5		dB
IMD₃	F = 860 MHz Vision = -8 dB Sound = -7 dB SB = -16 dB			-47	dB